MCR218-2, MCR218-4, MCR218-6

Preferred Device

Silicon Controlled Rectifiers

Reverse Blocking Thyristors

Designed primarily for half-wave ac control applications, such as motor controls, heating controls and power supplies; or wherever half-wave silicon gate-controlled, solid-state devices are needed.

Features

- Glass-Passivated Junctions
- Blocking Voltage to 400 Volts
- TO-220 Construction Low Thermal Resistance, High Heat Dissipation and Durability
- Pb–Free Packages are Available*

MAXIMUM RATINGS ($T_J = 25^{\circ}C$ unless otherwise noted)

Rating	Symbol	Value	Unit
Peak Repetitive Off–State Voltage (Note 1) (T _J = - 40 to 125°C, Gate Open) MCR218-2 MCR218-4 MCR218-6	V _{drm,} V _{rrm}	50 200 400	V
On-State RMS Current (180° Conduction Angles; T _C = 70°C)	I _{T(RMS)}	8.0	A
Peak Non-repetitive Surge Current (1/2 Cycle, Sine Wave 60 Hz, T_J = 125°C)	I _{TSM}	100	A
Circuit Fusing Considerations (t = 8.3 ms)	l ² t	26	A ² s
Forward Peak Gate Power (Pulse Width \leq 1.0 $\mu s,~T_C$ = 70°C)	P _{GM}	5.0	W
Forward Average Gate Power (t = 8.3 ms, $T_C = 70^{\circ}C$)	P _{G(AV)}	0.5	W
Forward Peak Gate Current (Pulse Width \leq 1.0 $\mu s,~T_C$ = 70°C)	I _{GM}	2.0	A
Operating Junction Temperature Range	TJ	-40 to +125	°C
Storage Temperature Range	T _{stg}	-40 to +150	°C

Maximum ratings are those values beyond which device damage can occur. Maximum ratings applied to the device are individual stress limit values (not normal operating conditions) and are not valid simultaneously. If these limits are exceeded, device functional operation is not implied, damage may occur and reliability may be affected.

 V_{DRM} and V_{RRM} for all types can be applied on a continuous basis. Ratings apply for zero or negative gate voltage; however, positive gate voltage shall not be applied concurrent with negative potential on the anode. Blocking voltages shall not be tested with a constant current source such that the voltage ratings of the devices are exceeded.

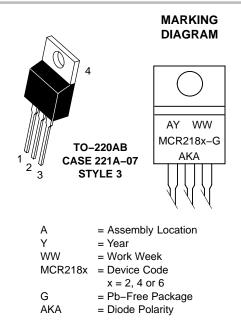


ON Semiconductor®

http://onsemi.com

SCRs 8 AMPERES RMS 50 thru 400 VOLTS





ORDERING INFORMATION

Device	Package	Shipping
MCR218-2	TO220AB	500 Units/Bulk
MCR218-2G	TO220AB (Pb–Free)	500 Units/Bulk
MCR218-4	TO220AB	500 Units/Bulk
MCR218-4G	TO220AB (Pb–Free)	500 Units/Bulk
MCR218-6	TO220AB	500 Units/Bulk
MCR218-6G	TO220AB (Pb–Free)	500 Units/Bulk

*For additional information on our Pb–Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

Preferred devices are recommended choices for future use and best overall value.

MCR218-2, MCR218-4, MCR218-6

THERMAL CHARACTERISTICS

Characteristic		Мах	Unit
Thermal Resistance, Junction-to-Case	$R_{ extsf{ heta}JC}$	2.0	°C/W
Maximum Lead Temperature for Soldering Purposes 1/8" from Case for 10 Seconds T _L 260		°C	

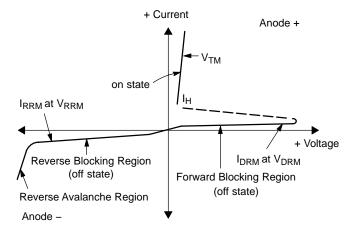
ELECTRICAL CHARACTERISTICS (T_J = 25° C unless otherwise noted.)

Characteristic	Symbol	Min	Тур	Max	Unit
DFF CHARACTERISTICS	·		•		•
Peak Repetitive Forward or Reverse Blocking Current	I _{DRM} , I _{RRM}				
$(V_{AK} = Rated V_{DRM} \text{ or } V_{RRM}, Gate Open)$ $T_J = 25^{\circ}C$		-	-	10	μΑ
T _J = 125°C		-	-	2.0	mA
DN CHARACTERISTICS					
Peak Forward On-State Voltage (Note 2) (I _{TM} = 16 A Peak)	V _{TM}	-	1.5	1.8	V
Gate Trigger Current (Continuous dc) $(V_D = 12 \text{ V}, \text{ R}_L = 100 \text{ Ohms})$	I _{GT}	-	10	25	mA
Gate Trigger Voltage (Continuous dc) $(V_D = 12 \text{ V}, \text{ R}_L = 100 \text{ Ohms})$	V _{GT}	-	-	1.5	V
Gate Non–Trigger Voltage (Rated 12 V, R_L = 100 Ohms, T_J = 125°C)	V _{GD}	0.2	-	-	V
Holding Current (V _D = 12 Vdc, Initiating Current = 200 mA, Gate Open)	Ι _Η	-	16	30	mA
DYNAMIC CHARACTERISTICS					
Critical Rate-of-Rise of Off-State Voltage (V _D = Rated V _{DRM} , Exponential Waveform, Gate Open, T _J = 125°C)	dv/dt	-	100	-	V/µs

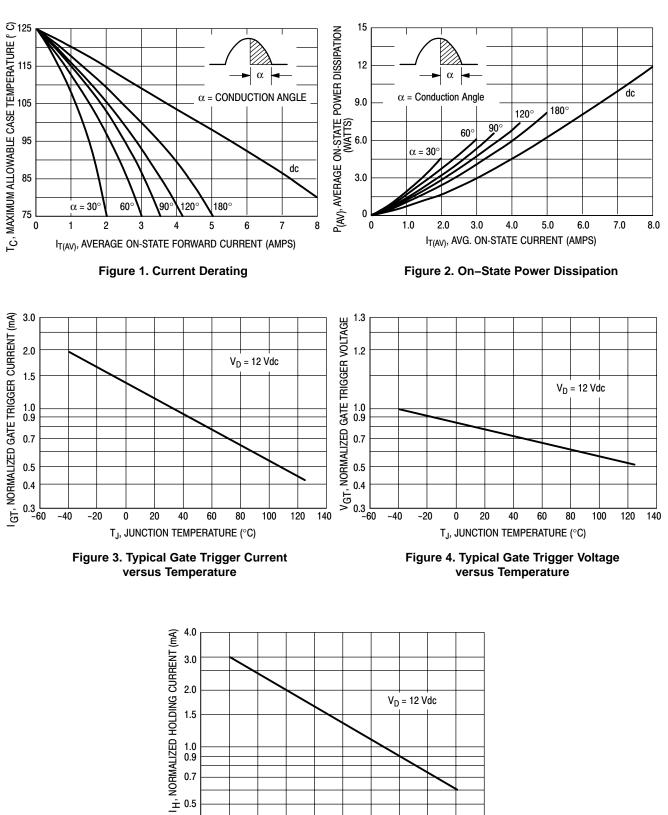
2. Pulse Test: Pulse Width = 1.0 ms, Duty Cycle \leq 2%.

Voltage Current Characteristic of SCR

Symbol	Parameter
V _{DRM}	Peak Repetitive Off State Forward Voltage
I _{DRM}	Peak Forward Blocking Current
V _{RRM}	Peak Repetitive Off State Reverse Voltage
I _{RRM}	Peak Reverse Blocking Current
V _{TM}	Peak On State Voltage
Ι _Η	Holding Current



MCR218-2, MCR218-4, MCR218-6



0.4 └ -60

-40

-20

0

20

40

T_J, JUNCTION TEMPERATURE (°C) Figure 5. Typical Holding Current versus Temperature

60

80

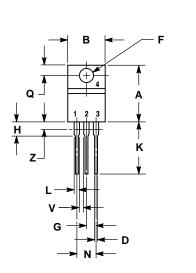
100

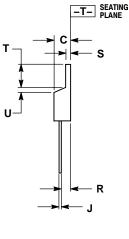
120

140

PACKAGE DIMENSIONS

TO-220AB CASE 221A-07 **ISSUE AA**





NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.

2. CONTROLLING DIMENSION: INCH. 3. DIMENSION Z DEFINES A ZONE WHERE ALL BODY AND LEAD IRREGULARITIES ARE

	INC	HES	MILLIN	IETERS
DIM	MIN	MAX	MIN MA	
Α	0.570	0.620	14.48	15.75
В	0.380	0.405	9.66	10.2
С	0.160	0.190	4.07	4.8
D	0.025	0.035	0.64	0.8
F	0.142	0.147	3.61	3.73
G	0.095	0.105	2.42	2.6
н	0.110	0.155	2.80	3.93
J	0.014	0.022	0.36	0.5
Κ	0.500	0.562	12.70	14.2
Г	0.045	0.060	1.15	1.5
Ν	0.190	0.210	4.83	5.3
Q	0.100	0.120	2.54	3.04
R	0.080	0.110	2.04	2.79
s	0.045	0.055	1.15	1.3
Т	0.235	0.255	5.97	6.4
U	0.000	0.050	0.00	1.2
۷	0.045		1.15	
Ζ		0.080		2.04

PIN 1. CATHODE ANODE 2. 3. GATE 4 ANODE

ON Semiconductor and 💷 are registered trademarks of Semiconductor Components Industries, LLC (SCILLC). SCILLC reserves the right to make changes without further notice to any products herein. SCILLC makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does SCILLC assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. "Typical" parameters which may be provided in SCILLC data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. SCILLC does not convey any license under its patent rights nor the rights of others. SCILLC products are not designed, intended, or authorized for use as components in systems intended for surgical implant into the body, or other applications intended to support or sustain life, or for any other application in which the failure of the SCILLC product could create a situation where personal injury or death may occur. Should Buyer purchase or use SCILLC products for any such unintended or unauthorized application, Buyer shall indemnify and hold SCILLC and its officers, employees, subsidiaries, affiliates, and distributors harmless against all claims, costs, damages, and expenses, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized use, even if such claim alleges that SCILLC was negligent regarding the design or manufacture of the part. SCILLC is an Equal Opportunity/Affirmative Action Employer. This literature is subject to all applicable copyright laws and is not for resale in any manner.

PUBLICATION ORDERING INFORMATION

LITERATURE FULFILLMENT

Literature Distribution Center for ON Semiconductor P.O. Box 61312, Phoenix, Arizona 85082-1312 USA Phone: 480-829-7710 or 800-344-3860 Toll Free USA/Canada Fax: 480-829-7709 or 800-344-3867 Toll Free USA/Canada Email: orderlit@onsemi.com

N. American Technical Support: 800-282-9855 Toll Free USA/Canada

Japan: ON Semiconductor, Japan Customer Focus Center 2-9-1 Kamimeguro, Meguro-ku, Tokyo, Japan 153-0051 Phone: 81-3-5773-3850

ON Semiconductor Website: http://onsemi.com

Order Literature: http://www.onsemi.com/litorder

For additional information, please contact your local Sales Representative.

MCR218/D